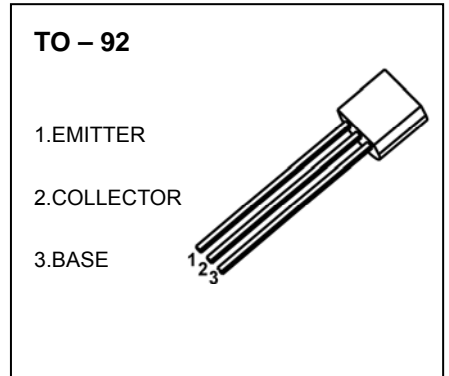


TO-92 Plastic-Encapsulate Transistors

D965V TRANSISTOR (NPN)

FEATURES

- General Purpose Switching and Amplification.



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	22	V
V _{CEO}	Collector-Emitter Voltage	15	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current	5	A
P _C	Collector Power Dissipation	750	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	166	°C/W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 1mA, I _E =0	22			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	15			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =10μA, I _C =0	6			V
Collector cut-off current	I _{CBO}	V _{CB} =20V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0			0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =2V, I _C =0.15mA	150			
	h _{FE(2)}	V _{CE} =2V, I _C =500mA	1200		2000	
	h _{FE(3)}	V _{CE} =2V, I _C =2A	150			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =3A, I _B =100mA			0.35	V
Transition frequency	f _T	V _{CE} =6V, I _C =50mA, f=30MHz	150			MHz